

## RF Power MOSFET Transistor 15W, 100-500 MHz, 28V

Rev. V1

### Features

- N-Channel enhancement mode device
- DMOS structure
- Lower capacitances for broadband operation
- Common source configuration
- Lower noise floor
- RoHS Compliant
- 100 MHz to 500 MHz operation

### ABSOLUTE MAXIMUM RATINGS AT 25° C

Parameter	Symbol	Rating	Units
Drain-Source Voltage	$V_{DS}$	65	V
Gate-Source Voltage	$V_{GS}$	20	V
Drain-Source Current	$I_{DS}$	4.2	A
Power Dissipation	$P_D$	48.6	W
Junction Temperature	$T_J$	200	°C
Storage Temperature	$T_{STG}$	-55 to 150	°C
Thermal Resistance	$\theta_{JC}$	3.6	°C/W

### TYPICAL DEVICE IMPEDANCES

F (MHz)	$Z_{IN}$ ( $\Omega$ )	$Z_{LOAD}$ ( $\Omega$ )
100	6.4-j25.0	22.0+j16.0
300	6.5-j12.0	15.0+j14.0
500	1.7-j10.5	8.0=j10.5

$V_{DD}=28V, I_{DQ}=150\text{ mA}, P_{OUT}=15.0\text{ W}$

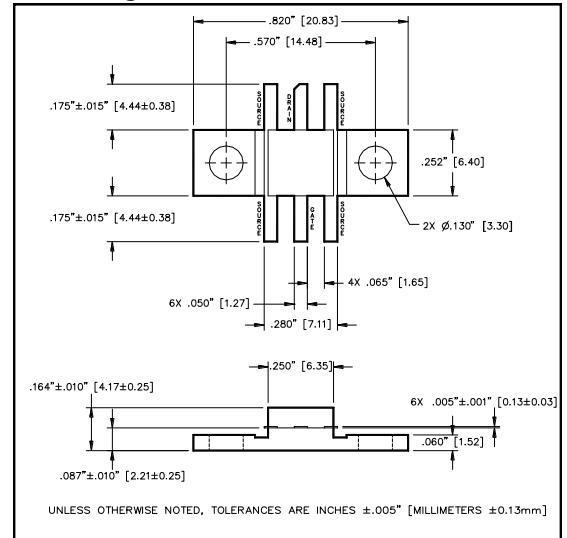
$Z_{IN}$  is the series equivalent input impedance of the device from gate to source.

$Z_{LOAD}$  is the optimum series equivalent load impedance as measured from drain to ground.

### ELECTRICAL CHARACTERISTICS AT 25°C

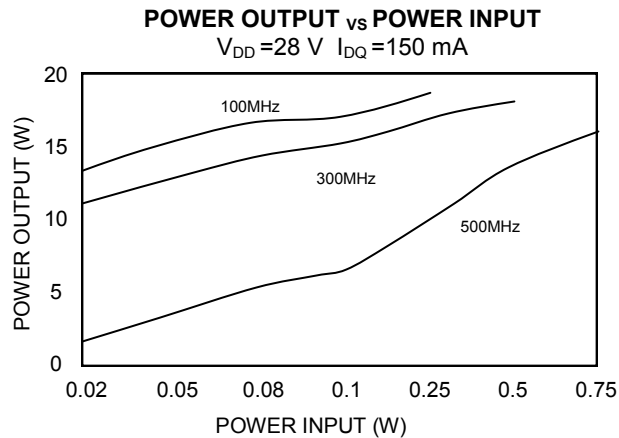
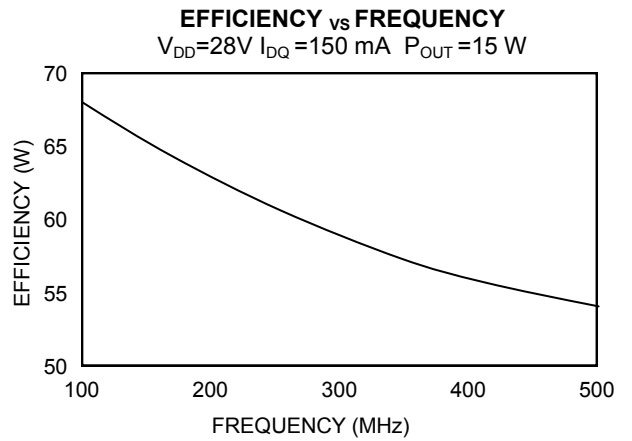
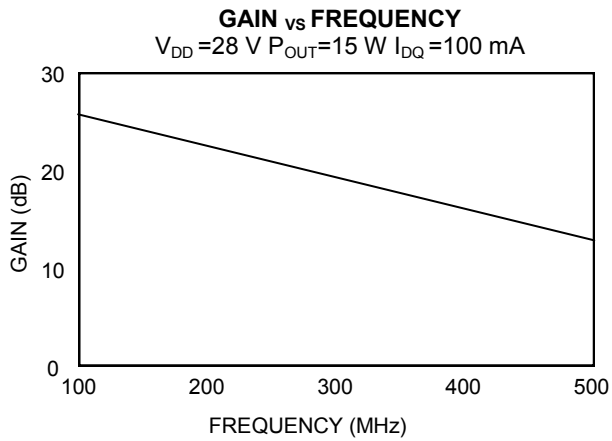
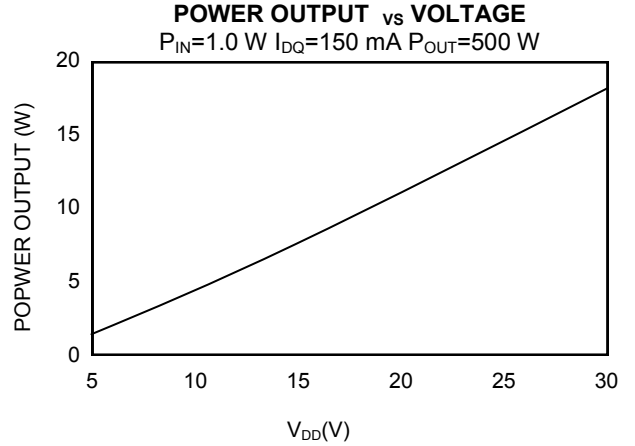
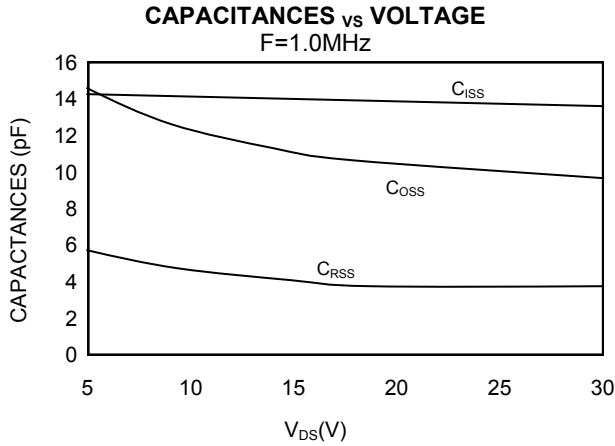
Parameter	Symbol	Min	Max	Units	Test Conditions
Drain-Source Breakdown Voltage	$BV_{DSS}$	65	-	V	$V_{GS} = 0.0\text{ V}, I_{DS} = 6.0\text{ mA}$
Drain-Source Leakage Current	$I_{DSS}$	-	3.0	mA	$V_{GS} = 28.0\text{ V}, V_{DS} = 0.0\text{ V}$
Gate-Source Leakage Current	$I_{GSS}$	-	3.0	$\mu\text{A}$	$V_{GS} = 20.0\text{ V}, V_{DS} = 0.0\text{ V}$
Gate Threshold Voltage	$V_{GS(TH)}$	2.0	6.0	V	$V_{DS} = 10.0\text{ V}, I_{DS} = 30.0\text{ mA}$
Forward Transconductance	$G_M$	.240	-	S	$V_{DS} = 10.0\text{ V}, I_{DS} = 300.0\text{ mA}, \Delta V_{GS} = 1.0V, 80\ \mu\text{s Pulse}$
Input Capacitance	$C_{ISS}$	-	21	pF	$V_{DS} = 28.0\text{ V}, F = 1.0\text{ MHz}$
Output Capacitance	$C_{OSS}$	-	15	pF	$V_{DS} = 28.0\text{ V}, F = 1.0\text{ MHz}$
Reverse Capacitance	$C_{RSS}$	-	7.2	pF	$V_{DS} = 28.0\text{ V}, F = 1.0\text{ MHz}$
Power Gain	$G_P$	10	-	dB	$V_{DD} = 28.0\text{ V}, I_{DQ} = 150.0\text{ mA}, P_{OUT} = 15.0\text{ W } F = 500\text{ MHz}$
Drain Efficiency	$\eta_D$	50	-	%	$V_{DD} = 28.0\text{ V}, I_{DQ} = 150.0\text{ mA}, P_{OUT} = 15.0\text{ W } F = 500\text{ MHz}$
Load Mismatch Tolerance	VSWR-T	-	20:1	-	$V_{DD} = 28.0\text{ V}, I_{DQ} = 150.0\text{ mA}, P_{OUT} = 15.0\text{ W } F = 500\text{ MHz}$

### Package Outline



LETTER DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	20.70	20.96	.815	.825
B	14.35	14.61	.565	.575
C	14.73	15.24	.580	.575
D	6.27	6.53	.247	.257
E	6.22	6.48	.245	.255
F	1.14	1.40	.045	.055
G	1.52	1.78	.060	.070
H	2.92	3.17	.115	.125
J	1.40	1.65	.055	.065
K	2.03	2.39	.080	.094
L	3.66	4.32	.144	.170
M	.10	.15	.004	.006

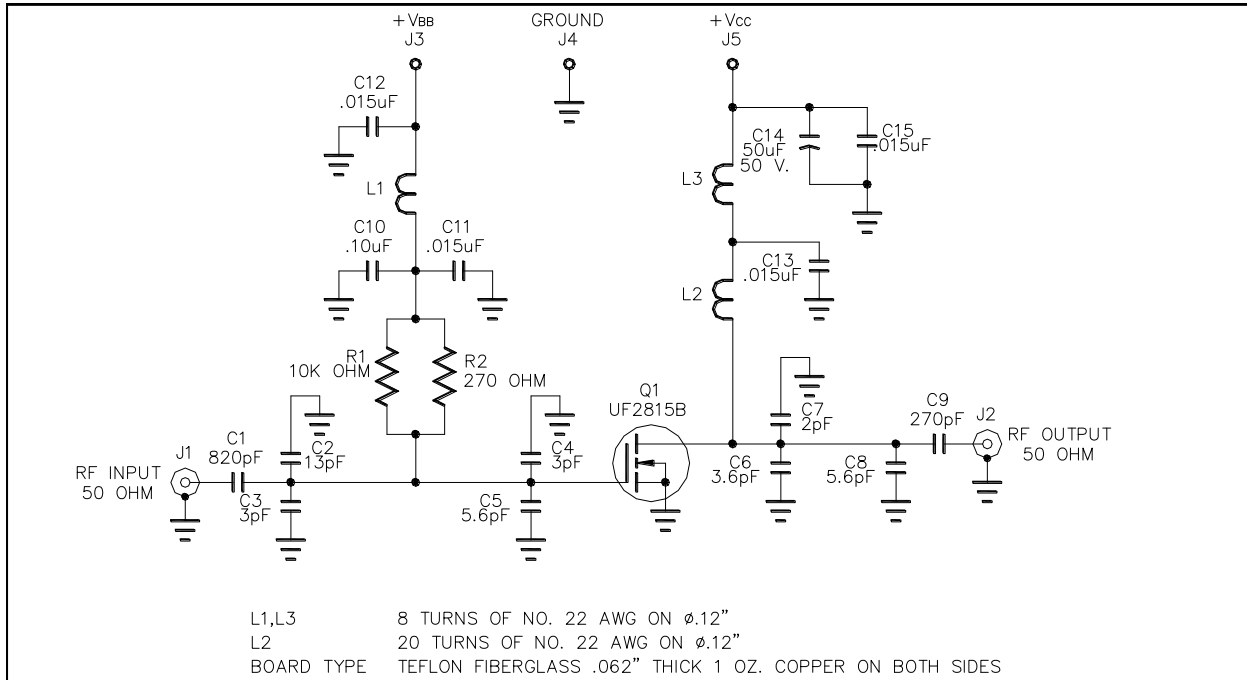
**Typical Broadband Performance Curves**



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### TEST FIXTURE SCHEMATIC



### TEST FIXTURE ASSEMBLY

